

## General Description

Din-Tek IGBTs offer low switching losses, high energy efficiency and high avalanche ruggedness for soft switching application such as IH(induction heating), microwave oven, etc.

## FEATURES

- High speed switching
- High system efficiency
- Soft current turn-off waveforms
- Extremely enhanced avalanche capability

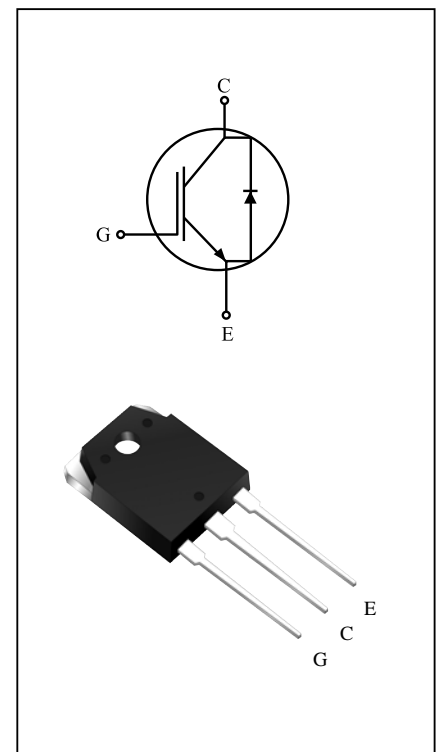
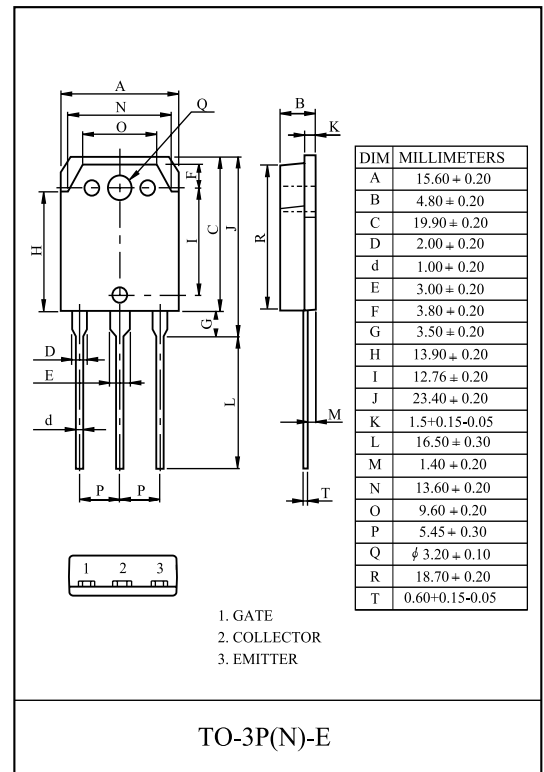
## MAXIMUM RATING (Ta=25 °C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Emitter Voltage		$V_{CES}$	1350	V
Gate-Emitter Voltage		$V_{GES}$	$\pm 20$	V
Collector Current	@T <sub>C</sub> =25	$I_C$	30	A
	@T <sub>C</sub> =100		15	A
Pulsed Collector Current		$I_{CM}^*$	45	A
Diode Continuous Forward Current	@T <sub>C</sub> =100	$I_F$	15	A
Diode Maximum Forward Current		$I_{FM}$	45	A
Maximum Power Dissipation	@T <sub>C</sub> =25	$P_D$	150	W
	@T <sub>C</sub> =100		60	W
Maximum Junction Temperature		$T_j$	150	
Storage Temperature Range		$T_{stg}$	-55 to + 150	

\*Repetitive rating : Pulse width limited by max. junction temperature

## THERMAL CHARACTERISTIC

CHARACTERISTIC	SYMBOL	MAX.	UNIT
Thermal Resistance, Junction to Case (IGBT)	$R_{thJC}$	0.82	/W
Thermal Resistance, Junction to Case (DIODE)	$R_{thJC}$	2.3	/W
Thermal Resistance, Junction to Ambient	$R_{thJA}$	40	/W



**ELECTRICAL CHARACTERISTICS** (Ta=25 )

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT	
Static							
Collector-Emitter Breakdown Voltage	BV <sub>CES</sub>	V <sub>GE</sub> =0V , I <sub>C</sub> =1.0mA	1350	-	-	V	
Collector Cut-off Current	I <sub>CES</sub>	V <sub>GE</sub> =0V, V <sub>CE</sub> =1200V	-	-	1.0	mA	
Gate Leakage Current	I <sub>GES</sub>	V <sub>CE</sub> =0V, V <sub>GE</sub> = ± 20V	-	-	± 100	nA	
Gate Threshold Voltage	V <sub>GE(th)</sub>	V <sub>GE</sub> =V <sub>CE</sub> , I <sub>C</sub> =15mA	4.5	6.0	7.5	V	
Collector-Emitter Saturation Voltage	V <sub>CE(sat)</sub>	V <sub>GE</sub> =15V, I <sub>C</sub> =15A	-	1.85	2.25	V	
		V <sub>GE</sub> =15V, I <sub>C</sub> =15A, T <sub>C</sub> = 125	-	2.15	-	V	
		V <sub>GE</sub> =15V, I <sub>C</sub> =30A	-	2.40	-	V	
Dynamic							
Total Gate Charge	Q <sub>g</sub>	V <sub>CC</sub> =600V, V <sub>GE</sub> =15V, I <sub>C</sub> = 15A	-	90	150	nC	
Gate-Emitter Charge	Q <sub>ge</sub>		-	15	-	nC	
Gate-Collector Charge	Q <sub>gc</sub>		-	40	-	nC	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>CC</sub> =600V, I <sub>C</sub> =15A, V <sub>GE</sub> =15V,R <sub>G</sub> =10 Inductive Load, T <sub>C</sub> = 25	-	30	-	ns	
Rise Time	t <sub>r</sub>		-	30	-	ns	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	150	-	ns	
Fall Time	t <sub>f</sub>		-	150	220	ns	
Turn-On Switching Loss	E <sub>on</sub>		-	2.1	-	mJ	
Turn-Off Switching Loss	E <sub>off</sub>		-	0.8	-	mJ	
Total Switching Loss	E <sub>ts</sub>		-	3.0	-	mJ	
Turn-On Delay Time	t <sub>d(on)</sub>		V <sub>CC</sub> =600V, I <sub>C</sub> =15A, V <sub>GE</sub> =15V, R <sub>G</sub> =10 Inductive Load, T <sub>C</sub> = 125	-	35	-	ns
Rise Time	t <sub>r</sub>			-	35	-	ns
Turn-Off Delay Time	t <sub>d(off)</sub>	-		180	-	ns	
Fall Time	t <sub>f</sub>	-		250	-	ns	
Turn-On Switching Loss	E <sub>on</sub>	-		2.5	-	mJ	
Turn-Off Switching Loss	E <sub>off</sub>	-		1.7	-	mJ	
Total Switching Loss	E <sub>ts</sub>	-		4.5	-	mJ	
Input Capacitance	C <sub>ies</sub>	V <sub>CE</sub> =30V, V <sub>GE</sub> =0V, f=1MHz	-	1600	-	pF	
Ouput Capacitance	C <sub>oes</sub>		-	60	-	pF	
Reverse Transfer Capacitance	C <sub>res</sub>		-	40	-	pF	

**ELECTRICAL CHARACTERISTIC OF DIODE**

CHARACTERISTIC	SYMBOL	TEST CONDITION		MIN.	TYP.	MAX.	UNIT
Diode Forward Voltage	V <sub>F</sub>	I <sub>F</sub> = 15A	T <sub>C</sub> =25	-	1.8	2.5	V
			T <sub>C</sub> =125	-	1.9	-	
Diode Reverse Recovery Time	t <sub>rr</sub>	I <sub>F</sub> = 15A di/dt = 200A/ μs	T <sub>C</sub> =25	-	230	300	ns
			T <sub>C</sub> =125	-	270	-	
Diode Peak Reverse Recovery Current	I <sub>rr</sub>		T <sub>C</sub> =25	-	24	31	A
			T <sub>C</sub> =125	-	27	-	
Diode Reverse Recovery Charge	Q <sub>rr</sub>		T <sub>C</sub> =25	-	2400	4000	nC
			T <sub>C</sub> =125	-	3640	-	

Fig 1. Saturation Voltage Characteristics

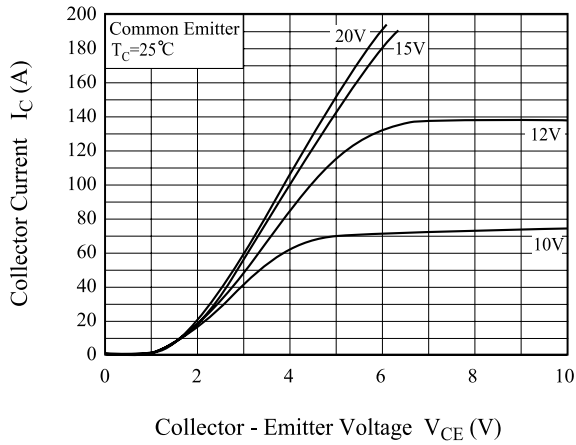


Fig 2. Saturation Voltage Characteristics

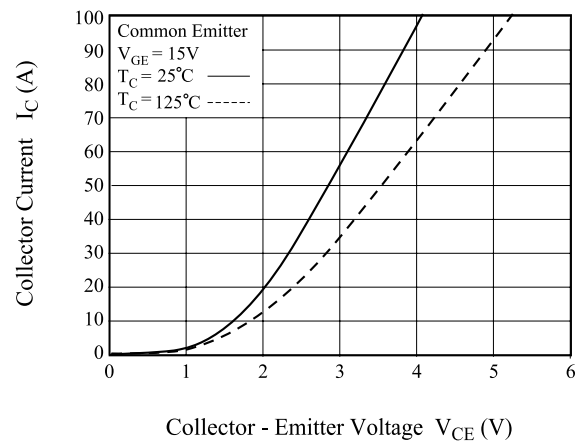


Fig 3. Saturation Voltage vs. Case Temperature

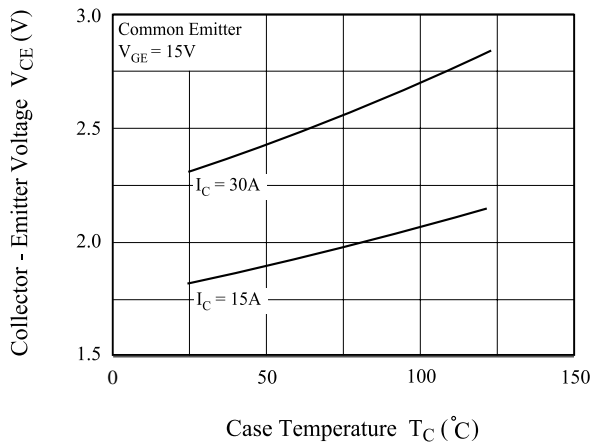


Fig 4. Saturation Voltage vs.  $V_{GE}$

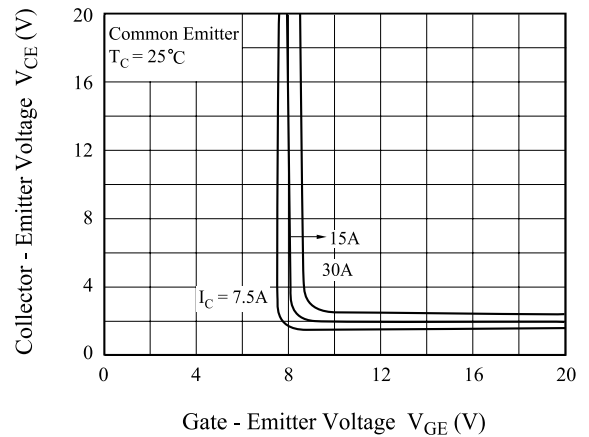


Fig 5. Saturation Voltage vs.  $V_{GE}$

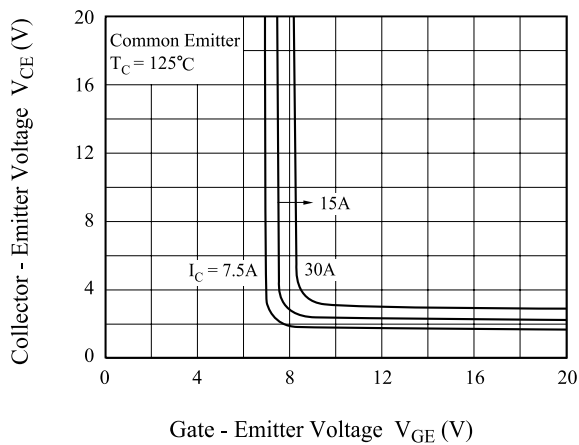


Fig 6. Capacitance Characteristics

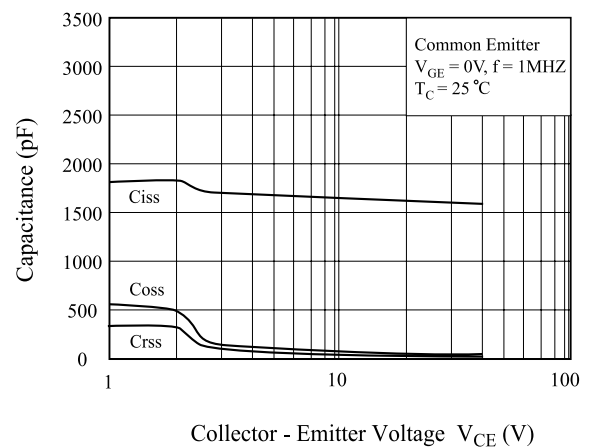


Fig 7. Turn-On Characteristics vs. Gate Resistance

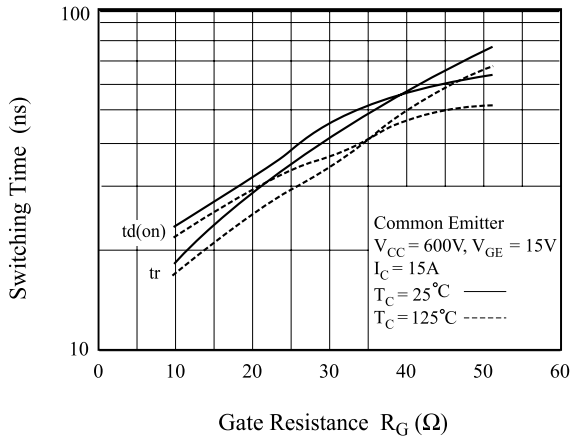


Fig 8. Turn-Off Characteristics vs. Gate Resistance

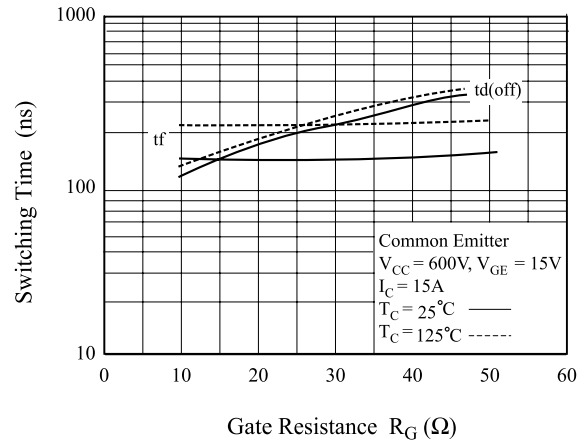


Fig 9. Switching Loss vs. Gate Resistance

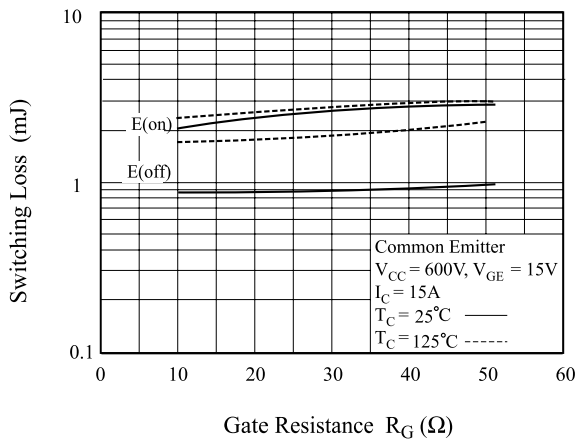


Fig 10. Turn-On Characteristics vs. Collector Current

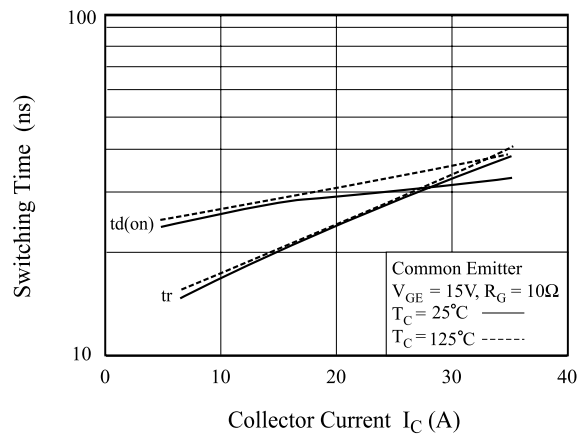


Fig 11. Turn-Off Characteristics vs. Collector Current

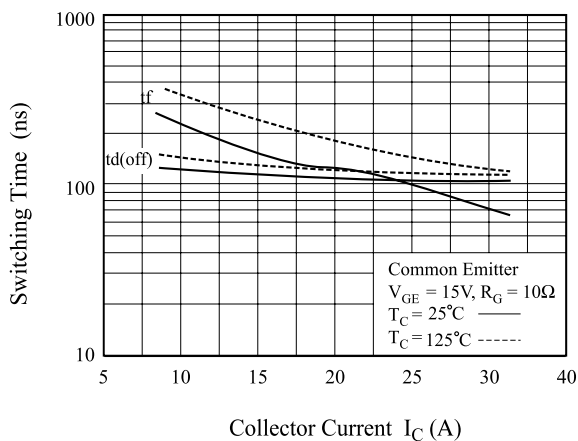


Fig 12. Switching Loss vs. Collector Current

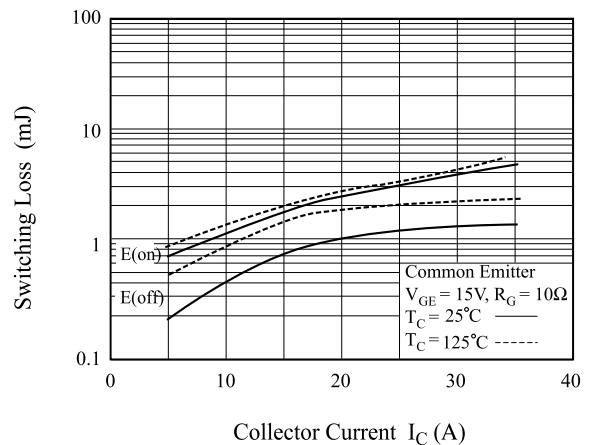


Fig 13. Gate Charge Characteristics

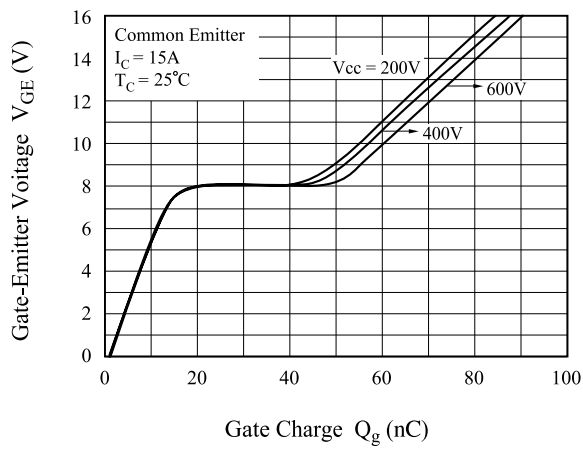


Fig 14. SOA Characteristics

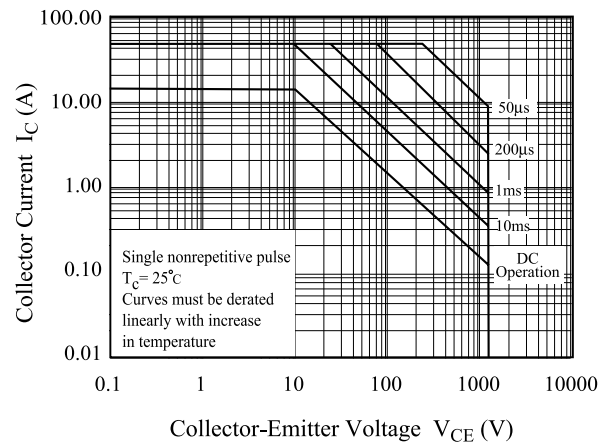


Fig 15. Turn-Off SOA

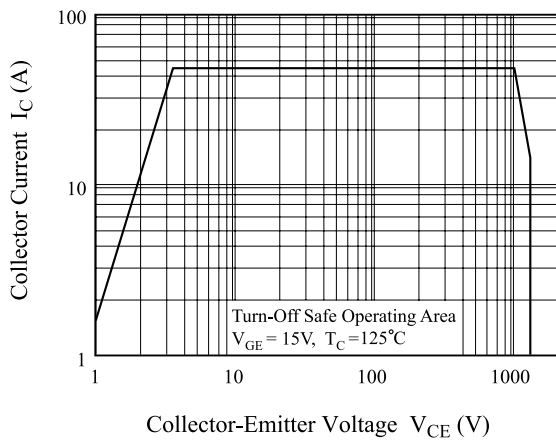


Fig 16. Transient Thermal Impedance of IGBT

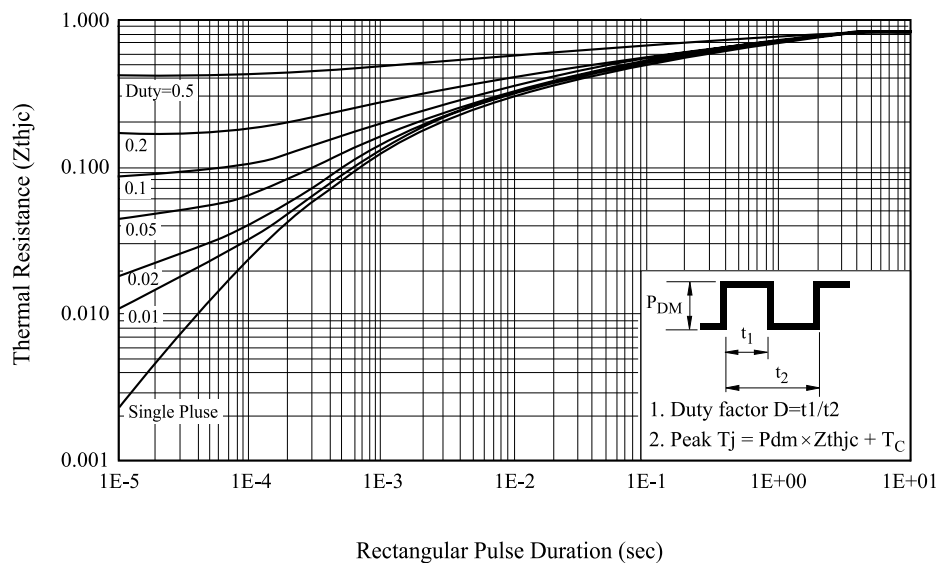


Fig 17. Forward Characteristics

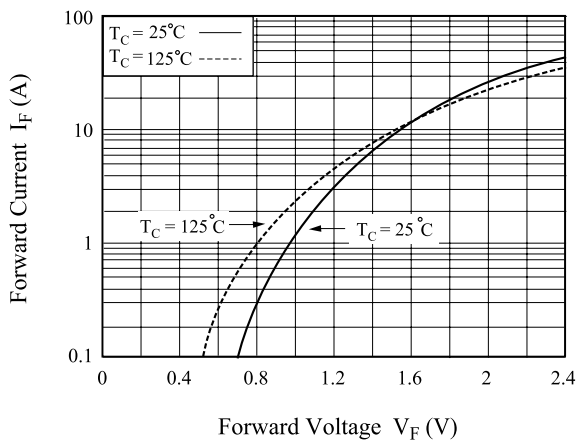


Fig 18. Reverse Recovery Current

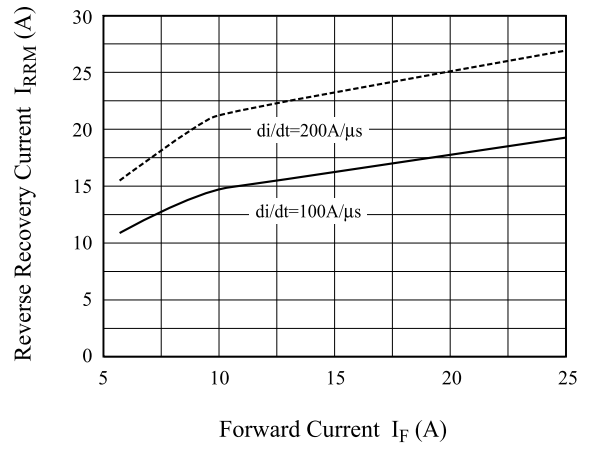


Fig 19. Reverse Recovery Time

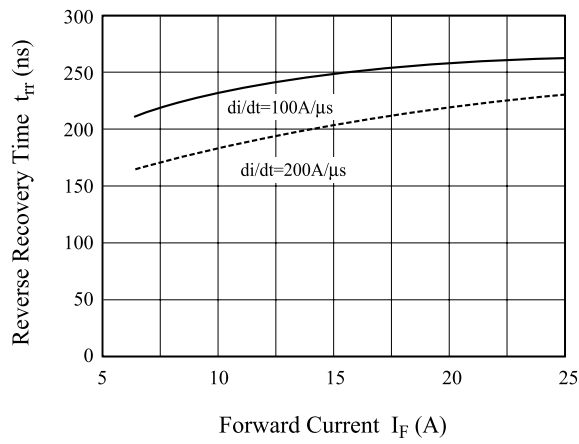


Fig 20. Switching Test Circuit

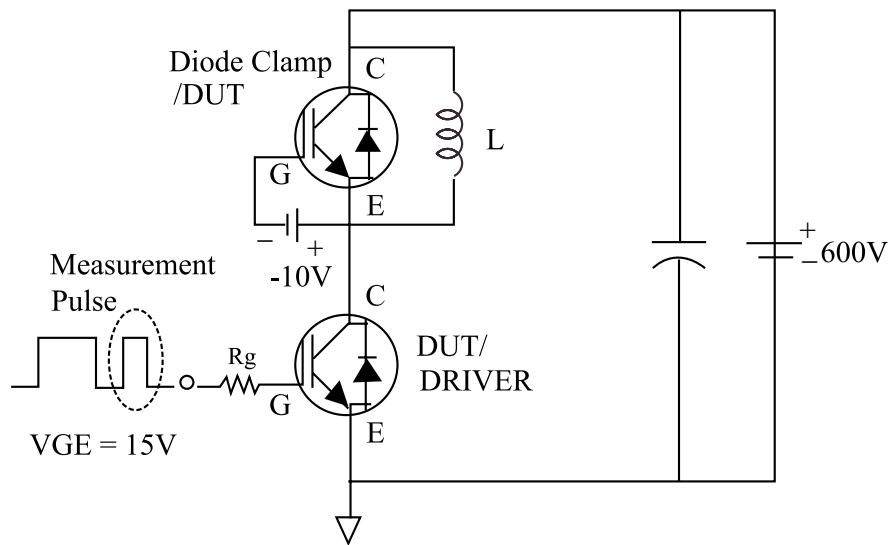


Fig 21. Definition Switching Time & Loss

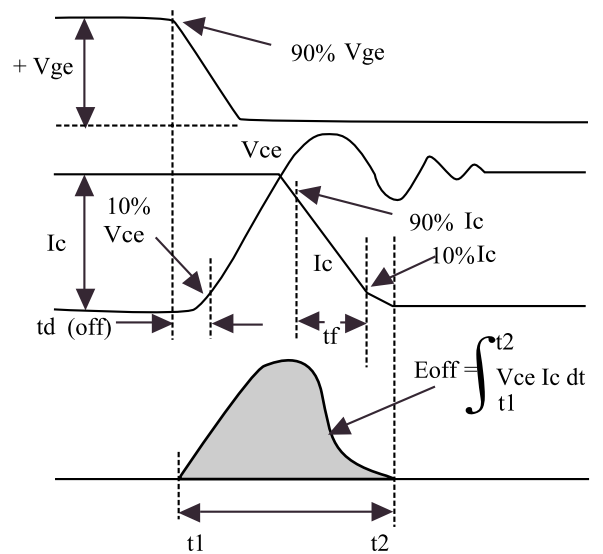
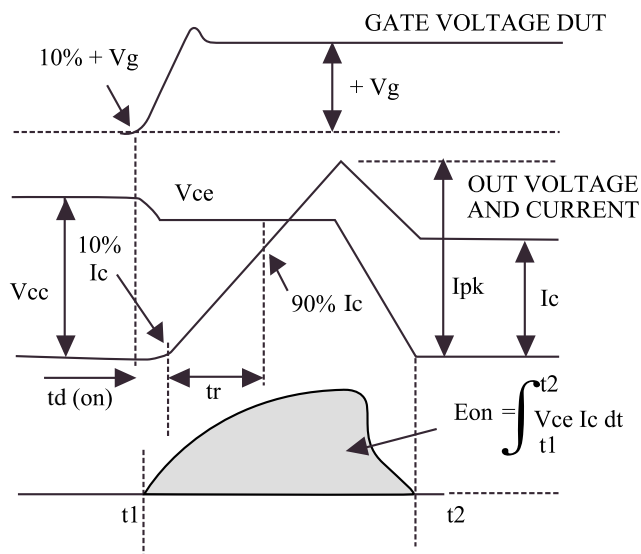
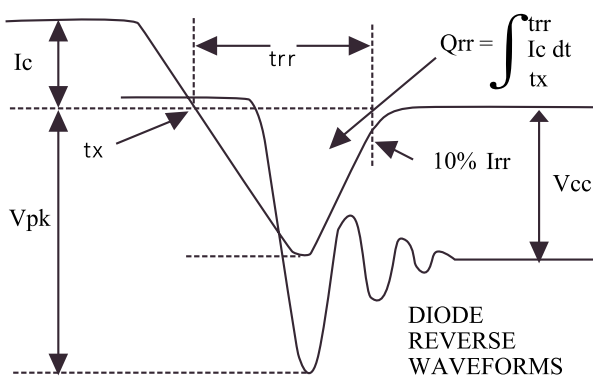
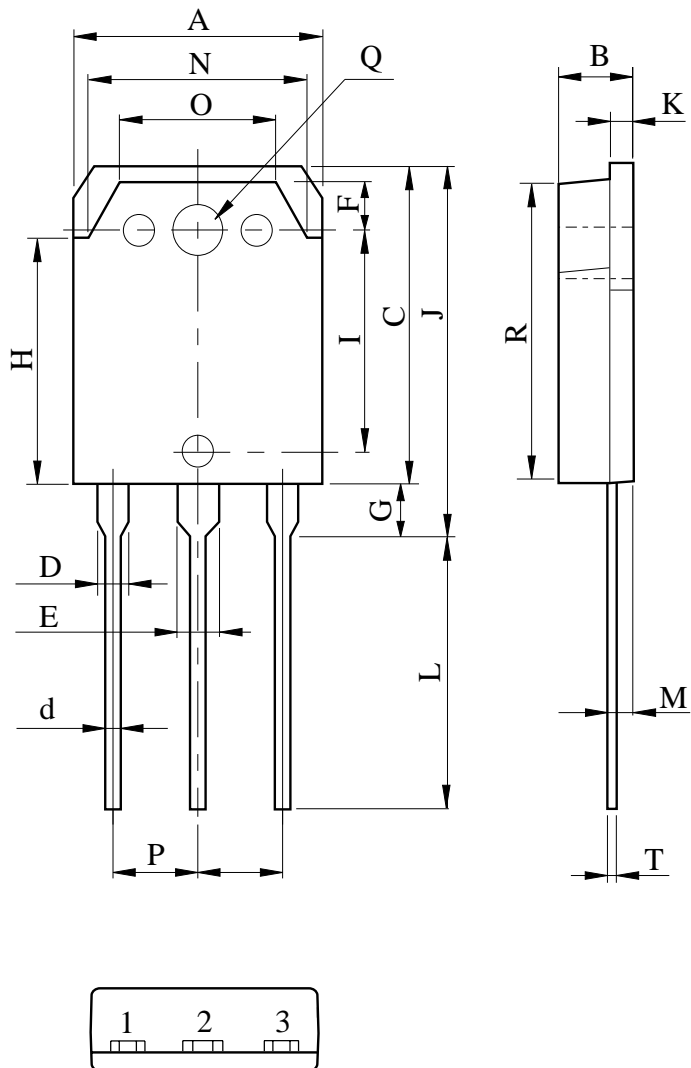


Fig 22. Definition Diode Switching Time





## TO-3P (High Voltage)



DIM	MILLIMETERS
A	$15.60 \pm 0.20$
B	$4.80 \pm 0.20$
C	$19.90 \pm 0.20$
D	$2.00 \pm 0.20$
d	$1.00 \pm 0.20$
E	$3.00 \pm 0.20$
F	$3.80 \pm 0.20$
G	$3.50 \pm 0.20$
H	$13.90 \pm 0.20$
I	$12.76 \pm 0.20$
J	$23.40 \pm 0.20$
K	$1.5+0.15-0.05$
L	$16.50 \pm 0.30$
M	$1.40 \pm 0.20$
O	$9.60 \pm 0.20$
P	$5.45 \pm 0.30$
Q	$\phi 3.20 \pm 0.10$
R	$18.70 \pm 0.20$
T	$0.60+0.15-0.05$

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